HiPerFRED

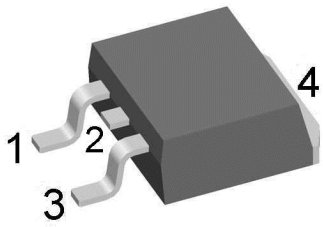
V_{RRM}	=	200 V
I_{FAV}	= 2x	15 A
t_{rr}	=	35 ns

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

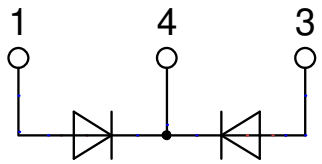
Part number

DPG30C200PC

Marking on Product: DPG30C200PC



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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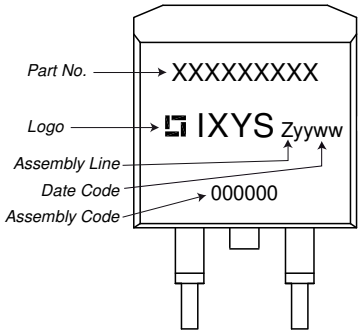
Fast Diode

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			200	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			200	V
I_R	*reverse current, drain current*	V_R = 200 V	T_{VJ} = 25°C			1	µA
		V_R = 200 V	T_{VJ} = 150°C			0.08	mA
V_F	*forward voltage drop*	I_F = 15 A	T_{VJ} = 25°C			1.26	V
		I_F = 30 A				1.51	V
		I_F = 15 A	T_{VJ} = 150°C			1.01	V
		I_F = 30 A				1.29	V
I_{FAV}	*average forward current*	T_C = 145°C	T_{VJ} = 175°C			15	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.69	V
r_F	*slope resistance* }					18	mΩ
R_{thJC}	*thermal resistance junction to case*					1.7	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.25		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			90	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			240	A
C_J	*junction capacitance*	V_R = 150 V f = 1 MHz	T_{VJ} = 25°C		20		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		3		A
		I_F = 15 A; V_R = 130 V	T_{VJ} = 125°C		6.5		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 130 A/µs	T_{VJ} = 25°C		35		ns
			T_{VJ} = 125°C		55		ns

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Package TO-263 (D2Pak)			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			35	A
T_{VJ}	*virtual junction temperature*		-55		175	°C
T_{op}	*operation temperature*		-55		150	°C
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
F_C	*mounting force with clip*		20		60	N

Product Marking



Part description

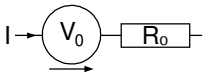
D = Diode
P = HiPerFRED
G = extreme fast
30 = Current Rating [A]
C = Common Cathode
200 = Reverse Voltage [V]
PC = TO-263AB (D2Pak) (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30C200PC-TRL	DPG30C200PC	Tape & Reel	800	506675
Alternative	DPG30C200PC-TUB	DPG30C200PC	Tube	50	525099

Similar Part	Package	Voltage class
DPG30C200PB	TO-220AB (3)	200
DPG30C200HB	TO-247AD (3)	200

Equivalent Circuits for Simulation

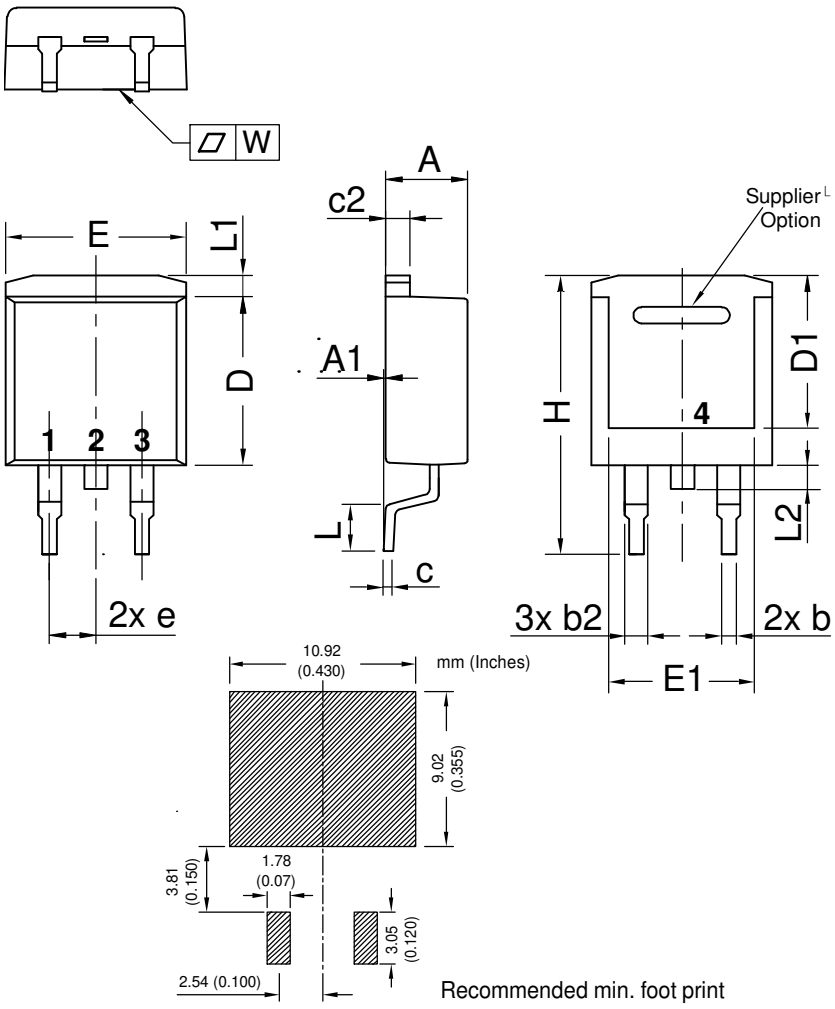
** on die level* $T_{VJ} = 175\,°C$



		Fast Diode	
$V_{0\,max}$	*threshold voltage*	0.69	V
$R_{0\,max}$	*slope resistance **	14.7	mΩ

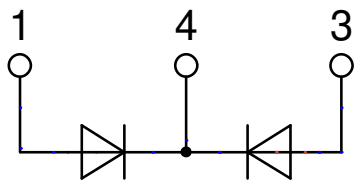
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Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



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Fast Diode

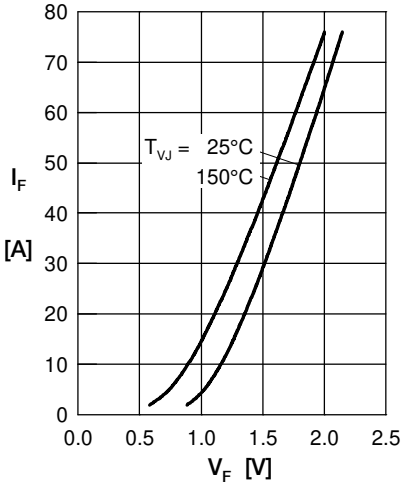


Fig. 1 Forward current I_F versus V_F

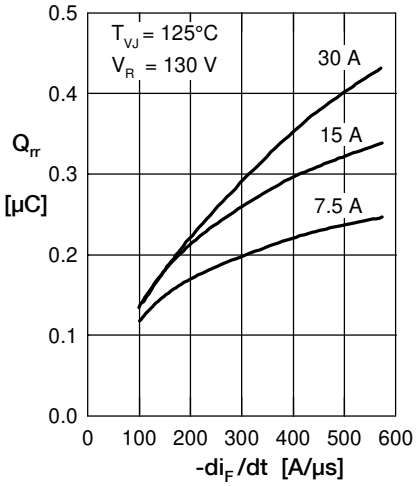


Fig. 2 Typ. reverse recov. charge Q_{rr} versus -di$_F$/dt

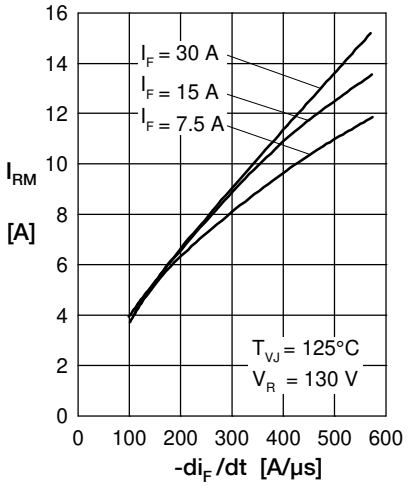


Fig. 3 Typ. peak reverse current I_{RM} versus -di$_F$/dt

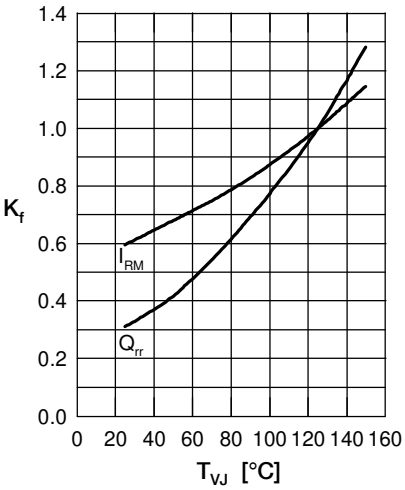


Fig. 4 Typ. dynamic parameters Q_{rr}, I_{RM} versus T_{VJ}

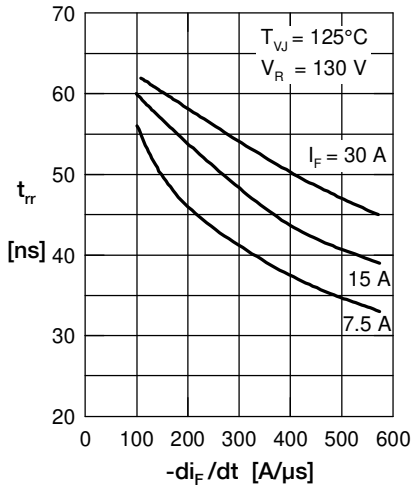


Fig. 5 Typ. recovery time t_{rr} versus -di$_F$/dt

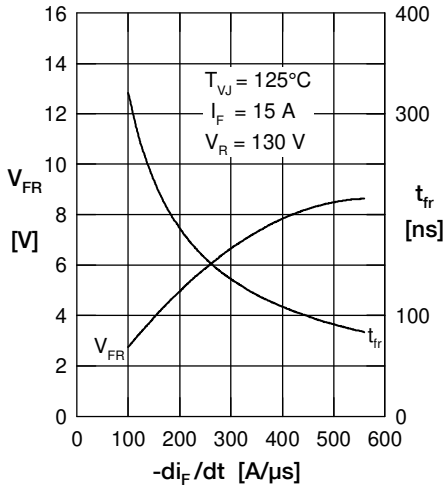


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di$_F$/dt

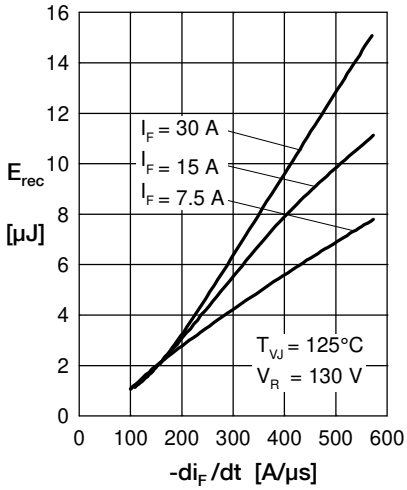


Fig. 7 Typ. recovery energy E_{rec} versus -di$_F$/dt

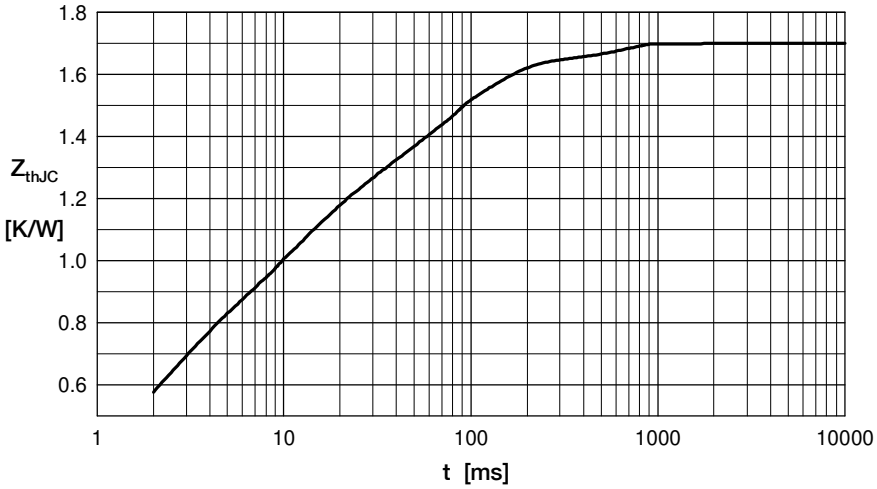


Fig. 8 Transient thermal resistance junction to case

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